

New Jersey Semi-Conductor Products Inc.

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SPRINGFIELD, NEW JERSEY 07081
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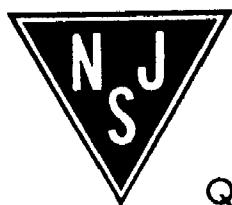
Germanium Transistors

2N1192

absolute maximum ratings: (25°C)

Voltage		
Collector to Base	V_{CEO}	-35 volts
Collector to Emitter	$V_{CEA} (R_{BE} \leq 10K)$	-25 volts
Emitter to Base	V_{EBO}	-10 volts
Current		
Collector	I_{CM}	-200 ma
Power		
Collector Dissipation*	P_c	200 mw
Temperature		
Storage	T_{STG}	-65 to +85 °C
Operating	T_J	+85 °C

*Derate 3.33 mw/°C increase in ambient temperature above 25°C.



Quality Semi-Conductors

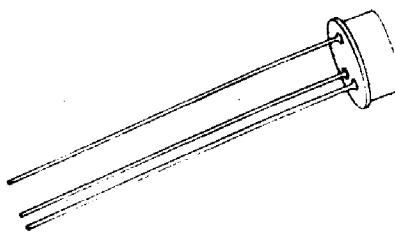
electrical characteristics: (25°C)

		Min.	Typ.	Max.
SMALL SIGNAL CHARACTERISTICS				
(Unless otherwise specified $V_C = -5V$ common base; $I_E = -1ma$; $f = 1000$ cps)				
Output Admittance (Input AC Open Circuited)	h_{o_b}	.1	.45	.9 μmho
Input Admittance (Output AC Short Circuited)	h_{i_b}	26	28	31 ohms
Reverse Voltage Transfer Ratio (Input AC Open Circuited)	h_{re}	1	5.9	14 $\times 10^{-1}$
Forward Current Transfer Ratio (Common Emitter; Output AC Short Circuited)	h_{fe}	60	80	120
Frequency Cutoff	f_{hrb}	1.5	4.2	mc
Output Capacity ($f = 1mc$; Input AC Open Circuited)	C_{ob}		26	40 μf
Noise Figure ($f = 1kc$; BW = 1 cycle)	NF		6	6 ⁺ db
D-C CHARACTERISTICS				
Forward Current Gain (Common Emitter, I_C/I_B) $(V_{CE} = -1V; I_C = -20ma)$ $(V_{CE} = -1V; I_C = -100ma)$	$\frac{h_{FE}}{h_{RE}}$	70	90	140
Collector Saturation Voltage ($I_C = -20ma$; I_B as indicated)	$V_{CE(\text{SAT})}$ $@ I_B =$		-90 -67	mv ma
Base Input Voltage, Common Emitter ($V_{BE} = -IV$; $I_C = -20ma$)	V_{BE}		-220	-260 volts
Collector Cutoff Current ($V_{CEO} = -30V$)	I_{EO}		-6	-12 μa
Emitter Cutoff Current ($V_{EBO} = -10V$)	I_{EO}		-4	-10 μa
Collector to Emitter Voltage ($R_{BE} = 10K$ ohms; $I_C = -.6ma$)	V_{CEB}	-25		volts

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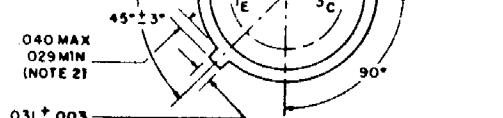
DIMENSIONS WITHIN JEDEC OUTLINE TO-5

NOTE 1: This zone is controlled for automatic handling. The variation in actual diameter within this zone shall not exceed .010.

NOTE 2: Measured from max. diameter of the actual device.

NOTE 3: The specified lead diameter applies in the zone between .050 and .250 from the base seal. Between .250 and .5 maximum of .021 diameter is held. Outside of these zones the lead diameter is not controlled. Leads may be inserted, without damage, in .031 holes while transistor enters .371 hole concentric with lead hole circle.

APPROX WEIGHT: .05 OZ
ALL DIMENSIONS IN INCHES



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